Dual SPST Analog Switch, Low Voltage, Single Supply

The NLAS325 is a dual SPST (Single Pole, Single Throw) switch, similar to 1/2 a standard 4066. The device permits the independent selection of 2 analog/digital signals. Available in the Ultra–Small 8 package.

The use of advanced 0.6 μ CMOS process, improves the R_{ON} resistance considerably compared to older higher voltage technologies.

Features

- On Resistance is 20 Ω Typical at 5.0 V
- Matching is $< 1.0 \Omega$ Between Sections
- 2.0-6.0 V Operating Range
- Ultra Low < 5.0 pC Charge Injection
- Ultra Low Leakage < 1.0 nA at 5.0 V, 25°C
- Wide Bandwidth > 200 MHz, -3.0 dB
- 2000 V ESD (HBM)
- R_{ON} Flatness $\pm 6.0 \Omega$ at 5.0 V
- Independent Enables; One Positive, One Negative
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

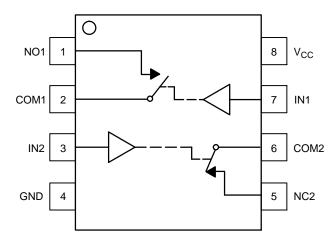


Figure 1. Pinout

1



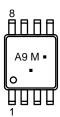
ON Semiconductor®

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US8 US SUFFIX CASE 493



A9 = Device Code

M = Date Code*

Pb-Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENT

1	NO1
2	COM1
3	IN2
4	GND
5	NC2
6	COM2
7	IN1
8	V _{CC}

FUNCTION TABLE

On/Off Enable Input	Analog Switch 1	Analog Switch 2
L	Off	On
Н	On	Off

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 9 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
VI	DC Input Voltage		-0.5 to +7.0	V
Vo	DC Output Voltage		-0.5 to +7.0	V
I _{IK}	DC Input Diode Current	V _I < GND	-50	mA
I _{OK}	DC Output Diode Current	V _O < GND	-50	mA
I _O	DC Output Sink Current	±50	mA	
I _{CC}	DC Supply Current per Supply Pin		± 100	mA
I _{GND}	DC Ground Current per Ground Pin		±100	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1.0 mm from Case for 10 Second	ds	260	°C
TJ	Junction Temperature under Bias		+ 150	°C
θ_{JA}	Thermal Resistance (Note 1)		250	°C/W
P _D	Power Dissipation in Still Air at 85°C		250	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 200 N/A	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
- 2. Tested to EIA/JESD22-A114-A.
- 3. Tested to EIA/JESD22-A115-A.
- 4. Tested to JESD22-C101-A.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CC}	DC Supply Voltage	2.0	5.5	V	
V _{IN}	Digital Select Input Voltage		GND	5.5	V
V _{IS}	Analog Input Voltage (NC, NO, COM)		GND	V _{CC}	V
T _A	Operating Temperature Range		-55	+ 125	°C
t _r , t _f	Input Rise or Fall Time, SELECT V	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0	100 20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

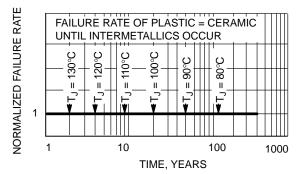


Figure 2. Failure Rate vs. Time Junction Temperature

DC CHARACTERISTICS - Digital Section (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Condition	V _{CC}	−55°C to 25°C	<85°C	<125°C	Unit
V _{IH}	Minimum High-Level Input		2.0	1.5	1.5	1.5	V
	Voltage, Select Inputs		2.5	1.9	1.9	1.9	
			3.0	2.1	2.1	2.1	1
			4.5	3.15	3.15	3.15	
			5.5	3.85	3.85	3.85	İ
V _{IL}	Maximum Low-Level Input		2.0	0.5	0.5	0.5	V
	Voltage, Select Inputs		2.5	0.6	0.6	0.6	1
			3.0	0.9	0.9	0.9	1
			4.5	1.35	1.35	1.35	
			5.5	1.65	1.65	1.65	1
I _{IN}	Maximum Input Leakage Current, Select Inputs	V _{IN} = 5.5 V or GND	0 V to 5.5 V	±0.2	±2.0	±2.0	μΑ
I _{CC}	Maximum Quiescent Supply Current	Select and $V_{IS} = V_{CC}$ or GND	5.5	4.0	4.0	8.0	μΑ

DC ELECTRICAL CHARACTERISTICS - Analog Section

				Guaran	Guaranteed Limit			
Symbol	Parameter	Condition	v _{cc}	-55°C to 25°C	<85°C	<125°C	Unit	
R _{ON}	Maximum "ON" Resistance (Figures 16 – 22)	$V_{IN} = V_{IL} \text{ or } V_{IH}$ $V_{IS} = \text{GND to } V_{CC}$ $I_{IN}I \le 10 \text{ mA}$	2.5 3.0 4.5 5.5	85 45 30 25	95 50 35 30	105 55 40 35	Ω	
R _{FLAT(ON)}	ON Resistance Flatness (Figures 16 – 22)	$V_{IN} = V_{IL} \text{ or } V_{IH}$ $I_{IN}I \le 10 \text{ mA}$ $V_{IS} = 1.0 \text{ V}, 2.0 \text{ V}, 3.5 \text{ V}$	4.5	4.0	4.0	5.0	Ω	
I _{NC(OFF)} I _{NO(OFF)}	NO or NC Off Leakage Current (Figure 8)	$V_{IN} = V_{IL} \text{ or } V_{IH}$ $V_{NO} \text{ or } V_{NC} = 1.0 \text{ V}_{COM} 4.5 \text{ V}$	5.5	1.0	10	100	nA	
I _{COM(ON)}	COM ON Leakage Current (Figure 8)	$\begin{split} &V_{IN} = V_{IL} \text{ or } V_{IH} \\ &V_{NO} \text{ 1.0 V or 4.5 V with } V_{NC} \text{ floating or } \\ &V_{NO} \text{ 1.0 V or 4.5 V with } V_{NO} \text{ floating } \\ &V_{COM} = 1.0 \text{ V or 4.5 V} \end{split}$	5.5	1.0	10	100	nA	

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$)

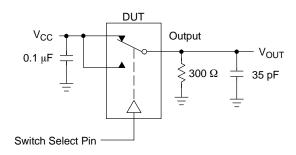
						Guaranteed Maximum Limit						
			V _{CC}	V _{IS}	-5	5°C to 2	25°C	<8	5°C	<12	25°C	•
Symbol	Parameter	Test Conditions	(V)	(V)	Min	Тур*	Max	Min	Max	Min	Max	Unit
t _{ON}	Turn-On Time	$R_L = 300 \Omega, C_L = 35 pF$	2.5	2.0	5.0	23	35	5.0	38	5.0	41	ns
	(Figures 11 and 12)	(Figures 4 and 5)	3.0	2.0	5.0	16	24	5.0	27	5.0	30	
			4.5	3.0	2.0	11	16	2.0	19	2.0	22	
			5.5	3.0	2.0	9.0	14	2.0	17	2.0	20	•
t _{OFF}	Turn-Off Time	$R_L = 300 \Omega, C_L = 35 pF$	2.5	2.0	1.0	7.0	12	1.0	15	1.0	18	ns
	(Figures 11 and 12)	(Figures 4 and 5)	3.0	2.0	1.0	5.0	10	1.0	13	1.0	16	
			4.5	3.0	1.0	4.0	6.0	1.0	9.0	1.0	12	
			5.5	3.0	1.0	3.0	5.0	1.0	8.0	1.0	11	•
t _{BBM}	Minimum Break-Before-Make	V _{IS} = 3.0 V (Figure 3)	2.5	2.0	1.0	12		1.0		1.0		ns
	Time	$R_L = 300 \Omega, C_L = 35 pF$	3.0	2.0	1.0	11		1.0		1.0		
			4.5	3.0	1.0	6.0		1.0		1.0		
			5.5	3.0	1.0	5.0		1.0		1.0		

^{*}Typical Characteristics are at 25°C.

		Typical @ 25, V _{CC} = 5.0 V	
C _{IN}	Maximum Input Capacitance, Select Input	8.0	pF
C _{NO} or C _{NC}	Analog I/O (switch off)	10	
C _{COM}	Common I/O (switch off)	10	
C _(ON)	Feedthrough (switch on)	20	

ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted)

			V _{CC}	Typical	
Symbol	Parameter	Condition	(V)	25°C	Unit
BW	Maximum On–Channel –3.0 dB Bandwidth or Minimum Frequency Response (Figure 10)	V_{IN} = 0 dBm V_{IN} centered between V_{CC} and GND (Figure 6)	3.0 4.5 5.5	145 170 175	MHz
V _{ONL}	Maximum Feedthrough On Loss	V_{IN} = 0 dBm @ 100 kHz to 50 MHz V_{IN} centered between V_{CC} and GND (Figure 6)	3.0 4.5 5.5	-2.0 -2.0 -2.0	dB
V _{ISO}	Off-Channel Isolation (Figure 9)	$ f = 100 \text{ kHz; } V_{\text{IS}} = 1.0 \text{ V RMS} $ $V_{\text{IN}} \text{ centered between } V_{\text{CC}} \text{ and GND} $ (Figure 6)	3.0 4.5 5.5	-93 -93 -93	dB
Q	Charge Injection Select Input to Common I/O (Figure 14)	$\begin{aligned} &V_{IN} = V_{CC\ to}\ GND,\ F_{IS} = 20\ kHz\\ &t_r = t_f = 3.0\ ns\\ &R_{IS} = 0\ \Omega,\ C_L = 1000\ pF\\ &Q = C_L\ ^*\Delta V_{OUT}\\ &(Figure\ 7) \end{aligned}$	3.0 5.5	1.5 3.0	pC
THD	Total Harmonic Distortion THD + Noise (Figure 13)	F_{IS} = 20 Hz to 100 kHz, R_L = Rgen = 600 Ω , C_L = 50 pF V_{IS} = 5.0 V_{PP} sine wave	5.5	0.1	%
VCT	Channel-to-Channel Crosstalk	$ f = 100 \text{ kHz; } V_{\text{IS}} = 1.0 \text{ V RMS} $ $V_{\text{IN}} \text{ centered between } V_{\text{CC}} \text{ and GND} $ (Figure 6)	5.5 3.0	- 90 - 90	dB



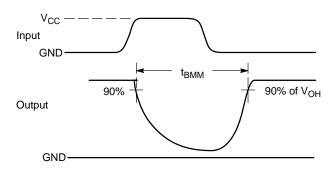
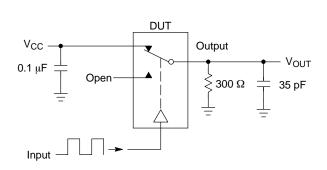


Figure 3. t_{BBM} (Time Break-Before-Make)



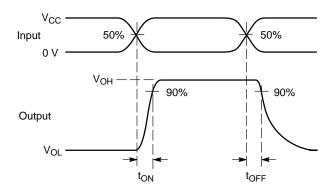
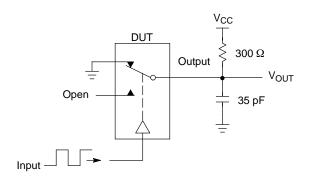


Figure 4. t_{ON}/t_{OFF}



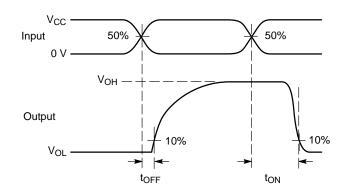
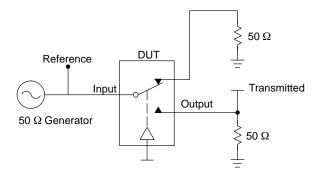


Figure 5. t_{ON}/t_{OFF}



Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. V_{ISO} , Bandwidth and V_{ONL} are independent of the input signal direction.

$$V_{ISO} = Off Channel Isolation = 20 Log \left(\frac{V_{OUT}}{V_{IN}}\right)$$
 or V_{IN} at 100 kHz

$$V_{ONL} = On \ Channel \ Loss = 20 \ Log \left(\frac{V_{OUT}}{V_{IN}} \right) \quad for \ V_{IN} \ at \ 100 \ kHz \ to \ 50 \ MHz$$

Bandwidth (BW) = the frequency 3.0 dB below V_{ONL}

 V_{CT} = Use V_{ISO} setup and test to all other switch analog input/outputs terminated with 50 Ω

Figure 6. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/V_{ONL}

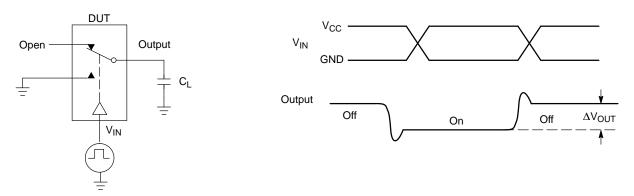


Figure 7. Charge Injection: (Q)

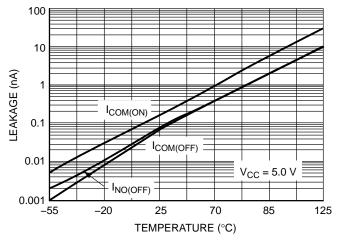
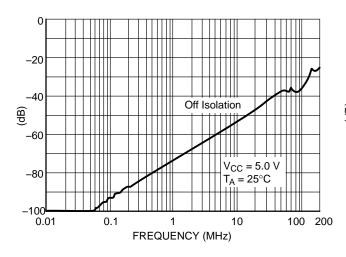


Figure 8. Switch Leakage vs. Temperature



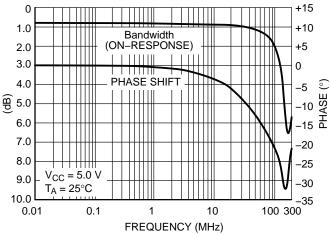


Figure 9. Off-Channel Isolation

Figure 10. Typical Bandwidth and Phase Shift

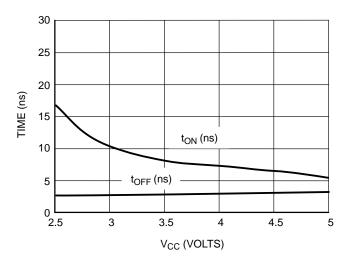


Figure 11. $t_{\mbox{\scriptsize ON}}$ and $t_{\mbox{\scriptsize OFF}}$ vs. $V_{\mbox{\scriptsize CC}}$ at 25°C

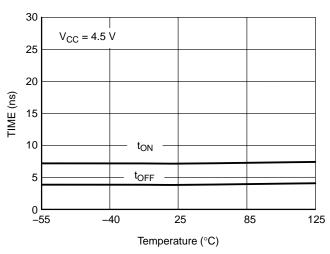


Figure 12. t_{ON} and t_{OFF} vs. Temp

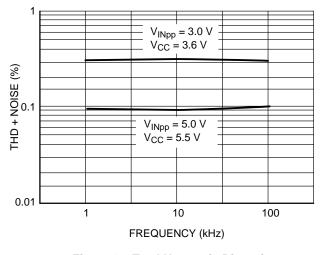


Figure 13. Total Harmonic Distortion Plus Noise vs. Frequency

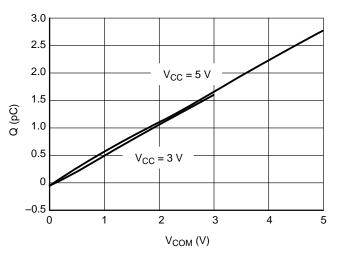
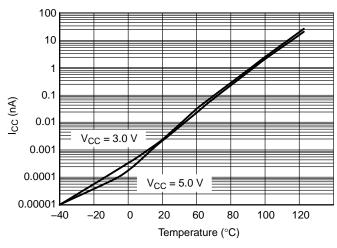


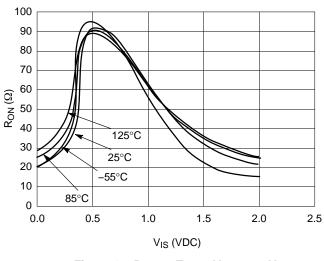
Figure 14. Charge Injection vs. COM Voltage



100 $V_{CC} = 2.0 \text{ V}$ 80 60 R_{ON} (Ω) V_{CC} = 2.5 V 40 $V_{CC} = 3.0 \text{ V}$ $V_{CC} = 4.0 V$ 20 0.0 1.0 2.0 3.0 4.0 5.0 6.0 V_{IS} (VDC)

Figure 15. I_{CC} vs. Temp, V_{CC} = 3.0 V and 5.0 V

Figure 16. R_{ON} vs. V_{CC} , Temp = 25°C



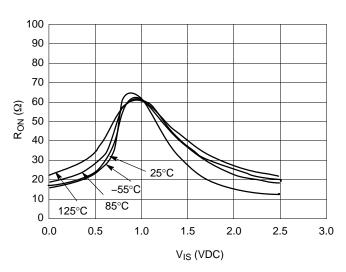
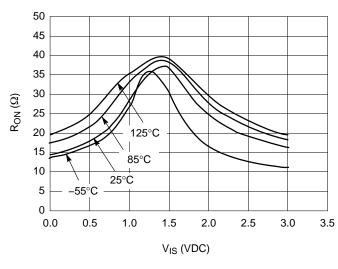


Figure 17. R_{ON} vs Temp, $V_{CC} = 2.0 \text{ V}$

Figure 18. R_{ON} vs. Temp, $V_{CC} = 2.5 \text{ V}$



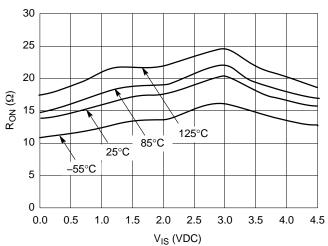
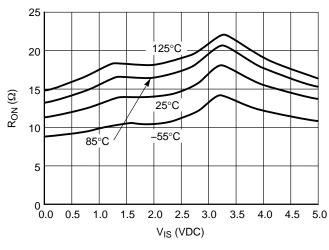


Figure 19. R_{ON} vs. Temp, V_{CC} = 3.0 V

Figure 20. R_{ON} vs. Temp, V_{CC} = 4.5 V



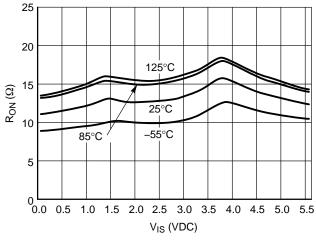


Figure 21. R_{ON} vs. Temp, $V_{CC} = 5.0 \text{ V}$

Figure 22. R_{ON} vs. Temp, V_{CC} = 5.5 V

ORDERING INFORMATION

Device Order Number	Package Type	Tape and Reel Shippingize†
NLAS325USG	US8 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

R R R R

В



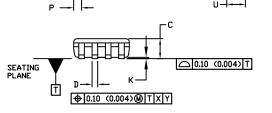


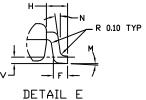
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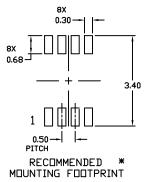
NOTES:

DETAIL E

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSION, OR GATE BURR. MOLD FLASH, PROTRUSION, OR GATE BURR SHALL NOT EXCEED 0.14 (0.0055°) PER SIDE.
- DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH AND PROTRUSION SHALL NOT EXCEED 0.14 (0.0055") PER SIDE.
- LEAD FINISH IS SOLDER PLATING WITH THICKNESS OF 0.0076-0.0203 MM (0.003-0.008").
- ALL TOLERANCE UNLESS OTHERWISE SPECIFIED ±0.0508 MM (0.002").





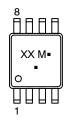


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— + — 3,40	
0.50 PITCH	
RECOMMENDED * MOUNTING FOOTPRINT	

	MUDINITING FULL FRIMI
*	For additional information on our Pb-Free strategy and soldering detalls, please download the DN Seniconductor Soldering and Mounting Techniques Reference Manual,

	MILLIMETERS		INCHES		
DIM	MIN.	MAX.	MIN.	MAX.	
Α	1.90	2.10	0.075	0.083	
В	5:50	2.40	0.087	0.094	
C	0.60	0.90	0.024	0.035	
D	0.17	0.25	0.007	0.010	
F	0.20	0.35	0.008	0.014	
G	0.50 BSC		0.020 BSC		
Н	0.40 REF		0.016 REF		
ſ	0.10	0.18	0.004	0.007	
K	0.00	0.10	0.000	0.004	
L	3.00	3.25	0.118	0.128	
М	0*	6*	0*	6*	
N	0*	10*	0*	10*	
Р	0.23	0.34	0.010	0.013	
R	0.23	0.33	0.009	0.013	
2	0.37	0.47	0.015	0.019	
U	0.60	0.80	0.024	0.031	
V	0.12 BSC		0.005 BSC		

GENERIC MARKING DIAGRAM*



XX = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	US8		PAGE 1 OF 1	

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FSA3051TMX NLAS4684FCTCG NLAS5223BLMNR2G NLX2G66DMUTCG 425541DB 425528R 099044FB NLAS5123MNR2G
PI5A4157CEX PI5A4599BCEX NLAS4717EPFCT1G PI5A3167CCEX SLAS3158MNR2G PI5A392AQE PI5A4157ZUEX
PI5A3166TAEX FSA634UCX XS3A1T3157GMX TC4066BP(N,F) DG302BDJ-E3 PI5A100QEX HV2605FG-G HV2301FG-G
RS2117YUTQK10 RS2118YUTQK10 RS2227XUTQK10 ADG452BRZ-REEL7 MAX4066ESD+ MAX391CPE+ MAX4730EXT+T
MAX314CPE+ BU4066BCFV-E2 MAX313CPE+ BU4S66G2-TR NLASB3157MTR2G TS3A4751PWR NLAST4599DFT2G
NLAST4599DTT1G DG300BDJ-E3 DG2503DB-T2-GE1 TC4W53FU(TE12L,F) HV2201FG-G 74HC2G66DC.125 DG3257DN-T1-GE4
ADG619BRMZ-REEL ADG1611BRUZ-REEL7 DG2535EDQ-T1-GE3 LTC201ACN#PBF 74LV4066DB,118 ISL43410IUZ